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Index
More Information

Index

1/*f* noise, 43–44

absorption coefficient, 10
absorption length, 10
acousto-optical modulator, 287
acousto-optical spectrometer, 293
Allan time, 335
antenna theorem, 296
AOM
  see acousto-optical modulator
AOS
  see acousto-optical spectrometer
avalanche photodiodes, 79–82
  noise, 79

backend spectrometer, 304
backends
  autocorrelation, 330
  discrete Fourier transform, 330
backshort, 307
bandpass filter, 6
BCS theory of superconductivity, 215
bipolar junction transistor, 99
blackbody, 2
blocked impurity band detectors, 84–91
bolometer examples
  Herschel PACS, 269
  hot electron, 272
  Planck HFI, 268
  room-temperature microbolometer, 247
  SCUBA-2, 270
bolometer noise
  Johnson, 256–257
  thermal, 257–259
bolometer, basic operation, 245–247
  heat capacity, 264–266
  NEP, 256
  quantum efficiency, 267–268
  simple thermal model, 245
  thermal link, 266–267
  thermal time constant, 246
Bose–Einstein statistics, 22
Bragg cell
  LO frequency shift, 287
  in AOS, 293

capacitance and inductance, complex representation, 106
CCD, 134–162
  anti-blooming gates, 147
  backside illumination, 155
  backside treatments, 156
  basic operation, 134–143
  buried channel, 143–148
  charge summing, 150
  charge transfer, 137
  charge transfer architectures, 149–150
  charge transfer efficiency, 140–143
  deep depletion, 157, 161
  electron multiplying, 154
  fat zero, 143
  floating diffusion readout, 152
  floating gate readout, 153
  frame transfer, 149
  frontside illumination, 154
  frontside pinning, 148
  interface trapping, 139, 143–144
  interline transfer, 149
  line address, 149
  orthogonal transfer, 150
  overclocking, 154
  quantum efficiency, 154
  quantum yield, 159
  readout, 150
  skipper readout, 154
  thinning, 155
  time-delay integration, 150
  UV and IR performance, 157

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CAMBRIDGE

Cambridge University Press
978-1-107-12414-1 — Detection of Light
George H. Rieke
Index
More Information

X-ray energy resolution, 159
X-ray performance, 158–162
charge coupled device
see CCD
classical mixer, 287
CMOS arrays, 125–127
active pixel sensors, 127
backside illumination, 127
Bayer pattern pixels, 126
comparison with CCDs, 126
passive pixel sensors, 127
coherent and incoherent performance comparison, 337
coherent detectors, 9
conversion gain, 314
conversion gain (mixer), 286
coplanar waveguide, 225
CTIA
see integrating amplifiers

D
see detectivity
D^*, 166, 277
Debye temperature, 265
DEPFET
see depleted P-channel FET
depleted P-channel FET, 127
sideways depletion, 128
detectivity, 166
DFT
see discrete Fourier transform
Dicke radiometer equation, 334
dielectric relaxation, 38–39
diffusion, 68–70
diffusion length, 70
diode
contact potential, 60
diode equation, 72
Fermi level, 60
principles, 59–61
diode equation, 94–97
diode mixers, 309–315
diplexer, 283
discrete Fourier transform, 330
DQE
see quantum efficiency
dynamic range, 10

effective wavelength, 6
Einstein relation, 70
electron optics, 187–206
in image intensifier, 198–206
in photomultiplier, 188–191
emissivity, 4
epitaxial growth, 65
extrinsic photoconductors, 48–54
background-dependent response, 53
impurity concentration limits, 49
ionizing radiation effects, 51
nonequilibrium response, 51
spiking, 53
stressed detectors, 50

Fano factor, 159
field effect transistor, 99–101
junction field effect transistor, 100
metal–oxide–semiconductor field effect transistor, 100
Fourier transforms, 17
Fourier transforms, table, 17
frequency bandwith, 41
frequency multiplication for LO, 329
frequency response, 17–19
future improvements in submm- and mm-wave receivers, 336

Geiger mode photodiodes, 82–83
generation–recombination noise, 40–41
germanium CCDs, 162
Gunn diode, 325
Gunn oscillator, 324

HEMT, 289
heterodyne, 303
heterodyne basics, 280–283
double sideband, 282
image signal, 282
intermediate frequency, IF, 282
local oscillator, LO, 281
mixer, 280
sidebands, 282
single sideband, 282
square law mixer, 281
heterodyne detector stage, 291
heterodyne receiver
total power detector, 292
heterodyne receiver definition, 279
heterodyne spatial arrays, 336
heterodyne system test procedures, 335
Y-factor, 335
heterodyne, spectral bandwidth, 294
high electron mobility transistor
see HEMT
high-energy X-ray detectors, 129
hot electron bolometer, 272–275
InSb, 272
superconducting, 273–275
hot electron bolometer mixers, 322–324

IBC detectors
dopants and spectral range, 84
gain, 90
operational properties, 89–91
quantum efficiency, 86–89
spectral response, 89
ideality factor, 75, 311
IF amplifier, 289

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CAMBRIDGE
Cambridge University Press
978-1-107-12414-1 — Detection of Light
George H. Rieke
Index
More Information

image intensifier, 196–206
  delay line readout, 203
  electron bombardment CCD, 203
  electronic readout, 202
  fiber optic bundles, 201
  Gen I, 199
  Gen II, 198
  ion events, 202
  magnetically focused, 199
  phosphor, 196
  proximity focused, 197
  resolution, 201
  source induced background, 201
imaging properties, 10, 13–17
  line pairs per millimeter, 13
  modulation transfer function, 14–17
  optical transfer function, 14
  spatial frequency, 14
IMPATT diodes, 327
impurity band conduction detectors, 84–91
indirect energy band, 30
infrared detector arrays, 120–125
  backside illumination, 122
  construction challenges, 122–123
  direct hybrid array, 121
  indium bump bonding, 120
  reference pixels, 116
  Z-plane technology, 121
integrating amplifiers, 109–120
  capacitive transimpedance amplifier, 112–114
  crosstalk, 118
  CTIA linearity, 113
  direct injection, 112
  double correlated sampling, 115
  dynamic range, 119
  electronic noise, 117–120
  Fowler sampling, 118
  kTC noise, 115–117
  multiaccum, 118
  nondestructive readout, 118
  read noise, 110
  readout strategies, 114–117
  reset noise, 115
  sampling up the ramp, 118
  simple source follower, 109–112
  source follower linearity, 111
  well depth, 110, 119
interpixel capacitance, 167
intrinsic photoconductors, 32–47
  material properties, 36
  spectral response, 37
IPC
  see interpixel capacitance
irradiance, 5

JFET, 100
Johnson noise, 42
junction field effect transistor
  see JFET

kTC noise, 43

LADAR, 283
Lambertian, 2
LIDAR, 283, 287
linearity, 10
load resistor readout, 102–103
local oscillators
  CO_2 laser, 288
  continuous wave laser, 283, 287–288
  Gunn diode, 324–327
  IMPATT diodes, 327
  MMICs, 328–329

MAMA
  see multi-anode microchannel array
MCP
  see microchannel plate
MESFET, 213, 289
metal oxide semiconductor field effect transistor
  see MOSFET
metal semiconductor field effect transistor
  see MESFET
microchannel plate, 195
microstrip, 225
microwave kinetic inductance detectors
  see MKIDs
millimeter-wave monolithic integrated circuit
  see MMIC
minimum detectable power, 299
mixer figure of merit, 308
MKIDs, 223–235
  $\lambda/4$ waveguide, 226
  applications, 235
  backshort, 232
  circuit behavior, 226
  detector arrays, 229
  lumped element, 224
  performance measurement, 234
  quality factor, Q, 226
  quantum efficiency, 231
  scattering matrix description, 228
  two-port device representation, 228
MMIC, 324, 328
MMIC local oscillators, 328
molecular beam epitaxy, 65
MOSFET, 100
MTF
  see imaging properties
multi-anode microchannel array, 203
multiplexer, 124
MUX
  see multiplexer

NEA
  see photocathode, negative electron affinity
NEP
  see noise equivalent power
noise, 10–13

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CAMBRIDGE

Cambridge University Press
978-1-107-12414-1 — Detection of Light
George H. Rieke
Index
More Information

noise combinations, 44–45
noise equivalent power, 166, 256
noise temperature, 300, 331–335
  receiver performance summary, 331
  system characterization, 332–335
Norton equivalent circuit, 105
Nyquist noise, 42

op-amp
  see operational amplifier
operational amplifier, 101–102
optical/infrared detector test procedures, 162–170
  calibrated sources, 163
  crosstalk, 169
  imaging performance, 168
  integrating amplifiers, 166
  laboratory blackbody sources, 163
  MTF, 168
  NEP, 166
  pixel gain, 166
  quartz tungsten halogen lamp, 163
  standard noise source, 166
  tunnel-trap diode configuration, 164
  waveform factor, 165

phosphor, 196
photocathode, 181–188
  dark current, 186–187
  electron affinity, 182
  negative electron affinity, 184
  quantum efficiency, 182, 184
  Richardson–Dushman equation, 186
  spectral response, 185
  work function, 181
photoconductors
  dielectric relaxation, 39
  frequency response, 38
  generation–recombination noise, 40
  latent images, 40
  photoconductive gain, 37
  responsivity, 36
photodetectors, 9
photodiode, 58–77
  capacitance, 76
  current and impedance, 72–75
  HgCdTe, 65–68
  materials, 64–65
  physics of operation, 68–77
  principles, 61–64
  quantum efficiency, 71–72
  response, 75
  ultraviolet, 64
  visible and infrared, 64
photoemissive detectors, 180–206
photography, 174–180
  color, 178
  detective quantum efficiency, 177
  development, 177
  dye sensitization, 178
  Gurney–Mott hypothesis, 176
  latent image, 177
  orthochromatic emulsions, 178
  panchromatic emulsions, 178
  photographic plate, 175
photomixer, 280
photomultiplier, 188–194
  detective quantum efficiency, 192
  dynode chain, 188–192
  electron multiplier, 190
  image dissector scanner, 190
  ion events, 187
  pulse counting, 192–193
  signal degradation in dynode chain, 190–192
  stability and linearity, 193–194
PIN photodiodes, 78
PMT
  see photomultiplier
pnCCD, 160
point spread function, 15
Poisson statistics, 11
polyphase filter bank, 330
primary antenna, 305
PSF
  see point spread function
pyroelectric detector, 249

QCD
  see quantum capacitance detector
QCL
  see quantum cascade laser
quantum capacitance detector, 241–242
quantum cascade laser, 288
quantum efficiency, 10–13
  detective, 12
  photon limited, 12
quantum limit, 298
quantum mixer, 286
quantum well detectors, 206–213
  bound-to-quasibound operation, 210
  heterojunction, 206
  MESFET readout, 213
  quantum well infrared photodetector, 207
  QWIP, 207
  spectral response, 211
  superlattice, 210
quantum yield, 129

R_0A product, 166
radiance, 2
radiant exitance, 2, 4
radiometric quantities, table, 7
random access, 125
reset noise, 43
room-temperature bolometer, 247–250
  Golay cell, 250
  microbolometer array readout, 248
  microbolometer arrays, 247–249

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CAMBRIDGE

Cambridge University Press
978-1-107-12414-1 — Detection of Light
George H. Rieke
Index
More Information

room-temperature bolometer (Cont.)
pyroelectric detectors, 249
thermopiles, 249

scalloping loss, 330
Schottky diode
design, 309
operation, 310
Schottky diode mixers, 309–315
conversion loss, 314
ideality factor, 311–312
performance, 312
performance limitations, 315
photolithographic, 309
point contact, 309
secondary antenna, 305
semiconductor bolometer, 250–260
electrothermal feedback, 253
neutron transmutation doped germanium, 251
readout, 260
responsivity, 253
temperature sensing, 251–252
time response, 252
semiconductors, 24–32
absorption coefficient, 30
band diagrams, 26
band gap, 26
compound semiconductors, 27
direct and indirect electron transitions, 30
electroluminescence, 30
Fermi level, 45
holes, 27
intrinsic and extrinsic, 27
traps and recombination centers, 29
valence and conduction bands, 26
single-mode detector, 306
SIS mixers, 315–322
construction, 315
conversion gain, 318
frequency bandwidth, 318–320
high-frequency limit, 320–321
I–V curve, 315–318
SNSPD
see superconducting nanowire single-photon detector
solar blind detectors, 65
solid angle, 4–5
solid state photomultiplier, 91
spectral bandwidth, 10
spectral radiance, 2, 4
spectral response, 10
SQUID, 222–223
Stefan–Boltzmann law, 4
STJ, 235–240
energy resolution, 238
Fano factor, 238
readout electronics, 239
superconducting bolometer, 260–264
electrothermal feedback, 262
frequency domain multiplexing, 263
multiplexing, 262–264
SQUID readout, 262
temperature sensing, 260–262
time domain multiplexing, 263
transition edge sensor, 260
superconducting electronics, 222–223
superconducting nanowire single-photon detector, 240–241
superconducting photodetectors, 9
superconducting quantum interference device
see SQUID
superconducting tunnel junction
see STJ
superconductivity principles, 215–221
“bandgap”, 216
Cooper pair, 216
critical temperature, 215
electrical resistance, 218–220
kinetic inductance, 220–221
London penetration depth, 219
Meissner effect, 218
quasiparticles, 216
superheterodyne, 303
SUR
see integrating amplifiers, sampling up the ramp

TDI
see CCD, time-delay integration
TES
see superconducting bolometer, transition edge sensor
Thévenin equivalent circuit, 105
thermal detectors, 9
thermal excitation, 45–47
thermal limit, 298
thermopile, 249
TIA
see transimpedance amplifier
time response, 10
transimpedance amplifier, 103–109
bias stability, 105
frequency response, 105–109
linearity, 104, 107
tunable diode laser LO, 288

vacuum photodiode, 180

waveguide, 307
white noise, 118
Wiedeman–Franz relation, 266

X-ray calorimeters, 271–272

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